

FORM PTO-1449 (Modified) U.S Dept. of Commerce (Rev. 7-80) Patent and Trademark Office				Atty Docket No. VEON-500 [FOV-123]		Appln. No. 10/621775 NEW	
INFORMATION DISCLOSURE CITATION							
(Use several sheets if necessary)							
				Applicant(s) EDISON FONG, et al.			
				Filing Date Herewith		Group 2858 Unknown	
U.S. PATENT DOCUMENTS							
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date
AD	AA	4,463,383	07/31/84	SONEDA et al.	358	212	05/05/82
AD	AB	6,480,227	11/12/02	YONEYAMA	348	308	03/30/98
	AC						
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*Examiner Initials		Document Number	Date	Country	Class	Subclass	Translation YES NO
	AD						
OTHER DOCUMENTS							
AD	AE	Fong, Edison, et al., "A High Performance 256K (512K) Static ROM," <u>IEEE Journal of Solid-State Circuits</u> , Vol. SC-18, No. 6, December 1983, pp. 807-810.					
AD	AF	Wong, Joseph, et al., "A 45 ns Fully Static 16K MOS ROM," <u>IEEE Journal of Solid-State Circuits</u> , Vol. SC-16, No. 5, pp. 592-594 (October 1981).					
AD	AG	Yang, David X.D., et al., "A Nyquist Rate Pixel Level ADC for CMOS Image Sensors," pages 1-4, downloaded from the Internet from http://www-isl.stanford.edu/~abbas/group/papers_and_pub/cicc.98.pdf (6/21/01).					
	AH	"Index of /~abbas/group/papers_and_pub," pages 1-4, downloaded from the Internet from http://www-isl.stanford.edu/~abbas/group/papers_and_pub/ on December 11, 2002.					
Examiner AD6				Date Considered 10/5/2004			
* Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							